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Kind regards,

Team Nexperia



# PMEG3010EP

# 1 A low V<sub>F</sub> MEGA Schottky barrier rectifier Rev. 01 — 30 December 2008

**Product data sheet** 

## **Product profile**

#### 1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD128 small and flat lead Surface-Mounted Device (SMD) plastic package.

#### 1.2 Features

- Average forward current: I<sub>F(AV)</sub> ≤ 1 A
- Reverse voltage: V<sub>R</sub> ≤ 30 V
- Low forward voltage
- High power capability due to clip-bond technology
- AEC-Q101 qualified
- Small and flat lead SMD plastic package

## 1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Low power consumption applications

#### 1.4 Quick reference data

Table 1. Quick reference data  $T_i = 25 \,^{\circ}C$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>F(AV)</sub>	average forward current	square wave; $\delta = 0.5$ ; $f = 20 \text{ kHz}$				
		T <sub>amb</sub> ≤ 130 °C	<u>[1]</u> -	-	1	Α
		T <sub>sp</sub> ≤ 145 °C	-	-	1	Α
$V_R$	reverse voltage		-	-	30	V
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 1 A	-	320	360	mV
I <sub>R</sub>	reverse current	$V_R = 30 \text{ V}$	-	0.6	1.5	mA
· ·						

<sup>[1]</sup> Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.



#### **Pinning information** 2.

Table 2. **Pinning** 

Pin	Description	Simplified outline	Graphic symbol
1	cathode	[1]	. [4]
2	anode	1 2	1 1 2
		<u> </u>	sym001

<sup>[1]</sup> The marking bar indicates the cathode.

#### **Ordering information** 3.

Table 3. **Ordering information** 

Type number	Package		
	Name	Description	Version
PMEG3010EP	-	plastic surface-mounted package; 2 leads	SOD128

# **Marking**

Table 4. **Marking codes** 

Type number	Marking code
PMEG3010EP	A1

# **Limiting values**

**Limiting values** Table 5.

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_R$	reverse voltage	T <sub>j</sub> = 25 °C	-	30	V
I <sub>F(AV)</sub>	average forward current	square wave; $\delta = 0.5$ ; f = 20  kHz			
		T <sub>amb</sub> ≤ 130 °C	<u>[1]</u> -	1	Α
		T <sub>sp</sub> ≤ 145 °C	-	1	Α
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; t <sub>p</sub> = 8 ms	[2] -	50	Α
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	[3][4]	625	mW
			[3][5]	1050	mW
			[3][1]	2100	mW



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#### 1 A low V<sub>F</sub> MEGA Schottky barrier rectifier

 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
T <sub>j</sub>	junction temperature		-	150	°C
$T_{amb}$	ambient temperature		-55	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

- [1] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [2]  $T_i = 25$  °C prior to surge.
- [3] Reflow soldering is the only recommended soldering method.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

#### 6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
- unig-a)	in free air	[1][2]				
junction to ambient			[3]	-	200	K/W
			<u>[4]</u> -	-	120	K/W
			<u>[5]</u> _	-	60	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		<u>[6]</u> _	-	12	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.
- [5] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- 6] Soldering point of cathode tab.

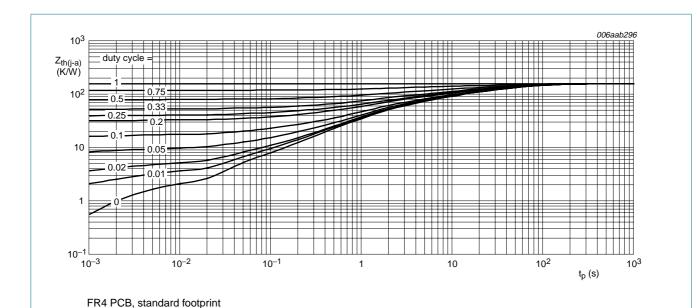
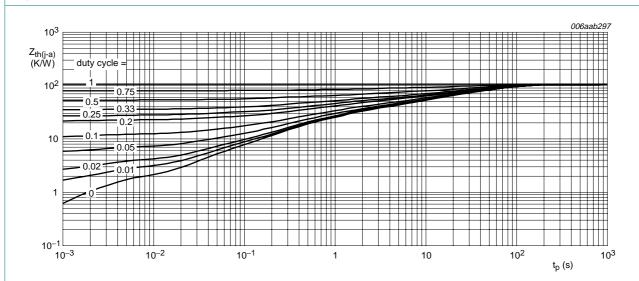
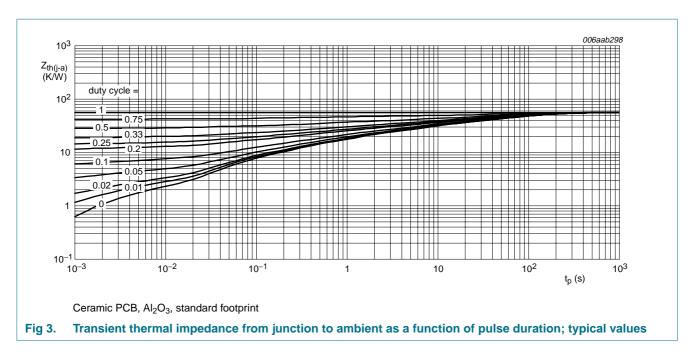


Fig 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



## 7. Characteristics

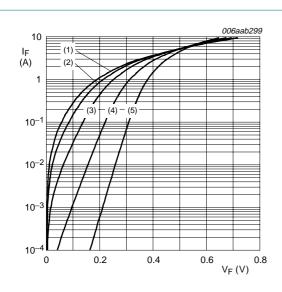
Table 7. Characteristics

 $T_i = 25 \,^{\circ}C$  unless otherwise specified.

$\begin{array}{cccccccccccccccccccccccccccccccccccc$	Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$I_F = 1 \text{ A}$ - 320 360 m <sup>2</sup> $I_R$ reverse current $V_R = 5 \text{ V}$ - 55 - $\mu A$	$V_{F}$	forward voltage	$I_F = 0.1 A$	-	230	260	mV
$I_R$ reverse current $V_R = 5 \text{ V}$ - $55 \text{ - } \mu A$		I <sub>F</sub> = 0.5 A	-	280	310	mV	
K -			I <sub>F</sub> = 1 A	-	320	360	mV
$V_R = 30 \text{ V}$ - 0.6 1.5 m/s	I <sub>R</sub>	reverse current	$V_R = 5 V$	-	55	-	μΑ
		$V_R = 30 \text{ V}$	-	0.6	1.5	mA	
$C_d$ diode capacitance $f = 1 \text{ MHz}$	$C_d$	diode capacitance	f = 1 MHz				
$V_R = 1 V$ - 170 - pF			$V_R = 1 V$	-	170	-	pF
$V_R = 10 \text{ V}$ - 60 - pF			V <sub>R</sub> = 10 V	-	60	-	pF

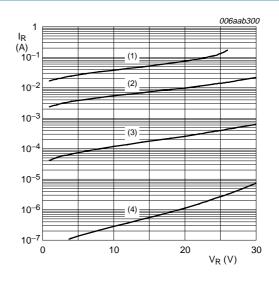
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## 1 A low V<sub>F</sub> MEGA Schottky barrier rectifier



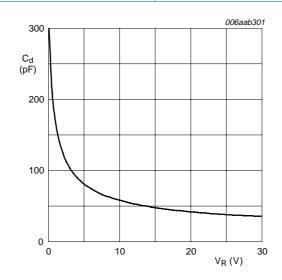
- (1)  $T_j = 150 \,^{\circ}\text{C}$
- (2)  $T_i = 125 \, ^{\circ}C$
- (3)  $T_i = 85 \,^{\circ}C$
- (4)  $T_j = 25 \, ^{\circ}C$
- (5)  $T_i = -40 \, ^{\circ}C$

Fig 4. Forward current as a function of forward voltage; typical values



- (1) T<sub>j</sub> = 125 °C
- (2)  $T_j = 85 \,^{\circ}C$
- (3)  $T_j = 25$  °C
- (4)  $T_j = -40 \, ^{\circ}C$

Fig 5. Reverse current as a function of reverse voltage; typical values

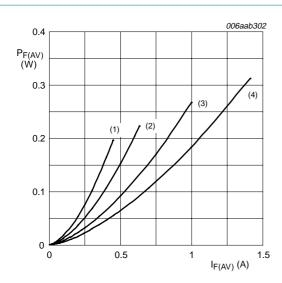


f = 1 MHz; T<sub>amb</sub> = 25 °C

**Product data sheet** 

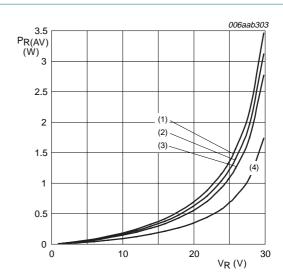
Fig 6. Diode capacitance as a function of reverse voltage; typical values

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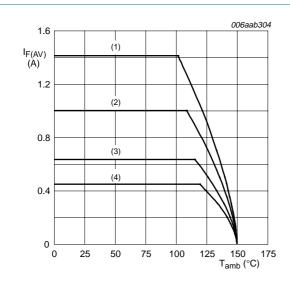
- (1)  $\delta = 0.1$
- (2)  $\delta = 0.2$
- (3)  $\delta = 0.5$
- (4)  $\delta = 1$

Average forward power dissipation as a Fig 7. function of average forward current; typical values



- (1)  $\delta = 1$
- (2)  $\delta = 0.9$
- (3)  $\delta = 0.8$
- (4)  $\delta = 0.5$

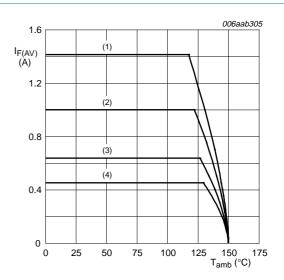
Fig 8. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

- (1)  $\delta = 1$ ; DC
- (2)  $\delta = 0.5$ ; f = 20 kHz
- (3)  $\delta = 0.2$ ; f = 20 kHz
- (4)  $\delta = 0.1$ ; f = 20 kHz

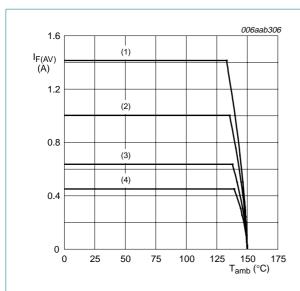
Average forward current as a function of Fig 9. ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

- (1)  $\delta = 1$ ; DC
- (2)  $\delta = 0.5$ ; f = 20 kHz
- (3)  $\delta = 0.2$ ; f = 20 kHz
- (4)  $\delta = 0.1$ ; f = 20 kHz

Fig 10. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

T<sub>i</sub> = 150 °C

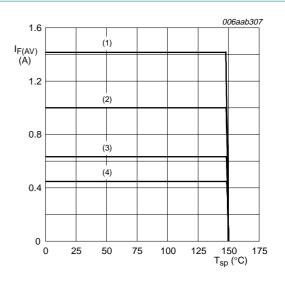
(1)  $\delta = 1$ ; DC

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig 11. Average forward current as a function of ambient temperature; typical values



T<sub>j</sub> = 150 °C

(1)  $\delta = 1$ ; DC

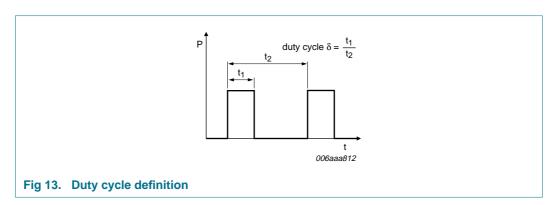
(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig 12. Average forward current as a function of solder point temperature; typical values

## 8. Test information

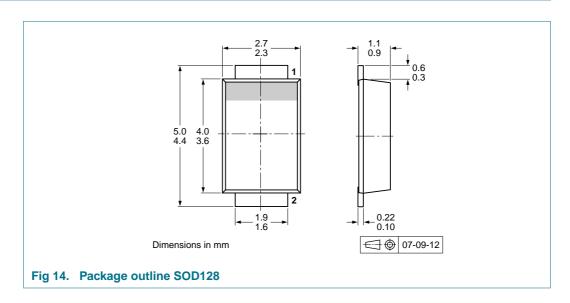


The current ratings for the typical waveforms as shown in Figure 9, 10, 11 and 12 are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

## 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

# 9. Package outline



# 10. Packing information

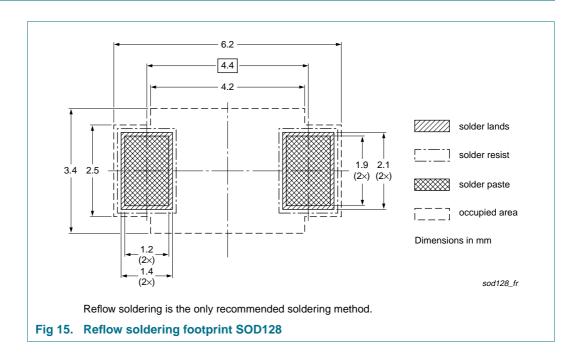
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity
			3000
PMEG3010EP	SOD128	4 mm pitch, 12 mm tape and reel	-115

<sup>[1]</sup> For further information and the availability of packing methods, see Section 14.

# 11. Soldering





# 12. Revision history

## Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG3010EP_1	20081230	Product data sheet	-	-

## 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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# PMEG3010EP

# 1 A low V<sub>F</sub> MEGA Schottky barrier rectifier

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